

# UNISONIC TECHNOLOGIES CO., LTD

3N40K-MT

#### **Preliminary**

**Power MOSFET** 

### 3A, 400V N-CHANNEL POWER MOSFET

#### **DESCRIPTION**

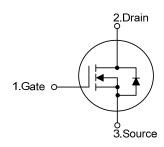
The UTC 3N40K-MT is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology specializes in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC 3N40K-MT is universally applied in electronic lamp ballast based on half bridge topology and high efficient switched mode power supply.

#### **FEATURES**

- \*  $R_{DS(ON)}$  < 2.00 @  $V_{GS}$  = 10 V,  $I_{D}$  = 1.5 A
- \* High switching speed
- \* 100% avalanche tested

#### **SYMBOL**

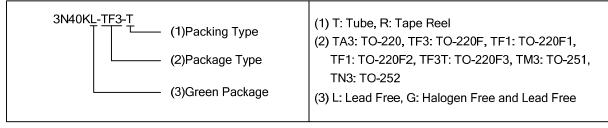


## TO-220 TO-220F1 TO-220F2 TO-220F3 TO-251 TO-252

#### ORDERING INFORMATION

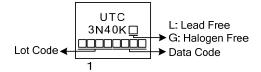
Ordering Number		Dookogo	Pin Assignment			Doolsing	
Lead Free	Halogen Free	Free Package		2	3	Packing	
3N40KL-TA3-T	3N40KG-TA3-T	TO-220	G	D	S	Tube	
3N40KL-TF3-T	3N40KG-TF3-T	TO-220F	G	D	S	Tube	
3N40KL-TF1-T	3N40KG-TF1-T	TO-220F1	G	D	S	Tube	
3N40KL-TF2-T	3N40KG-TF2-T	TO-220F2	G	D	S	Tube	
3N40KL-TF3T-T	3N40KG-TF3T-T	TO-220F3	G	D	S	Tube	
3N40KL-TM3-T	3N40KG-TM3-T	TO-251	G	D	S	Tube	
3N40KL-TN3-R	3N40KG-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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#### ■ MARKING



#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	400	V
Gate-Source Voltage		$V_{GSS}$	±30	V
Drain Current	Continuous (T <sub>C</sub> =25°C)	I <sub>D</sub>	3	Α
	Pulsed (Note 2)	I <sub>DM</sub>	12	Α
Avalanche Energy	Single Pulsed (Note 3)	E <sub>AS</sub>	290	mJ
	Repetitive (Note 2)	E <sub>AR</sub>	3	mJ
Power Dissipation	TO-220		54	W
	TO-220F/TO-220F1 TO-220F3	P <sub>D</sub>	25	W
	TO-220F2		26	W
	TO-251/TO-252		50	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T <sub>STG</sub>	-55~+150	°C

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

  Absolute maximum ratings are stress ratings only and functional device operation is not implied.
  - 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
  - 3. L=56mH,  $I_{AS}$ =3.0 A,  $V_{DD}$ =50V,  $R_{G}$ =25  $\Omega$ , Starting  $T_{J}$  = 25°C
  - 4.  $I_{SD} \le 4.4A$ , di/dt  $\le 200A/\mu s$ ,  $V_{DD} \le BV_{DSS}$ , Starting  $T_J = 25$ °C

#### ■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3	θја	62.5	°C/W
	TO-251/TO-252		110	°C/W
Junction to Case	TO-220		2.28	°C/W
	TO-220F/TO-220F1 TO-220F3	θυς	4.9	°C/W
	TO-220F2		4.8	°C/W
	TO-251/TO-252		2.5	°C/W

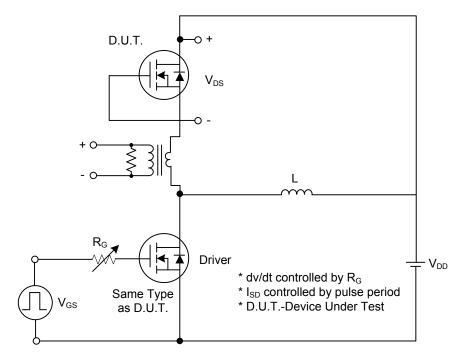
#### ■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS N		TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		$BV_{DSS}$	$I_D = 250 \mu A, V_{GS} = 0 V$	400			V
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS} / \triangle T_J$	Reference to 25°C, I <sub>D</sub> =250µA		0.38		V/°C
Drain-Source Leakage Current		I <sub>DSS</sub>	V <sub>DS</sub> =400V, V <sub>GS</sub> =0V			10	μΑ
Gate- Source Leakage Current	Forward		$V_{GS}$ =+30V, $V_{DS}$ =0V			+100	nA
	Reverse	I <sub>GSS</sub>	V <sub>GS</sub> =-30V, V <sub>DS</sub> =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	3.0		5.0	V
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =1.5A			2.0	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C <sub>ISS</sub>			248	350	pF
Output Capacitance		Coss	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz		40	80	pF
Reverse Transfer Capacitance		$C_{RSS}$			5	9	pF
SWITCHING PARAMETERS							
Turn-ON Delay Time		t <sub>D(ON)</sub>			40		ns
Rise Time		t <sub>R</sub>	$V_{DS}$ =30V, $I_{D}$ =0.5A, $R_{G}$ =25 $\Omega$		48		ns
Turn-OFF Delay Time		$t_{D(OFF)}$	(Note 1, 2)		48		ns
Fall-Time		$t_{F}$			27		ns
Total Gate Charge		$Q_G$	\\ -10\\ \\ -50\\   -1.30		12.3	15	nC
Gate to Source Charge		$Q_GS$	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =1.3A (Note 1, 2)		4.48		nC
Gate to Drain Charge		$Q_GD$	(Note 1, 2)		2.2		nC
SOURCE- DRAIN DIODE RATIF	NGS AND C	HARACTERIST	rics				
Maximum Body-Diode Continuous Current		$I_{SD}$				3.0	Α
Maximum Body-Diode Pulsed Current		I <sub>SM</sub>				12	Α
Drain-Source Diode Forward Voltage		$V_{SD}$	I <sub>S</sub> =3A, V <sub>GS</sub> =0V			1.5	V

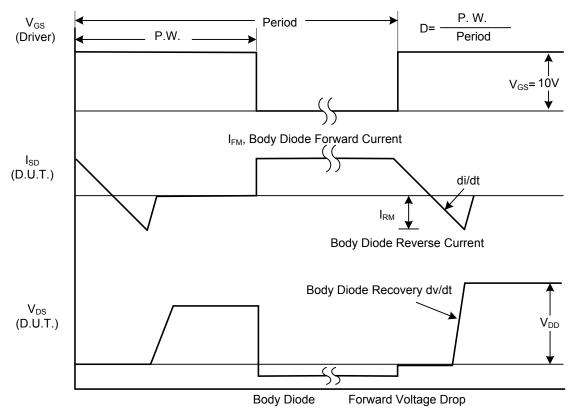
Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%

<sup>2.</sup> Essentially independent of operating temperature

#### TEST CIRCUITS AND WAVEFORMS



Peak Diode Recovery dv/dt Test Circuit

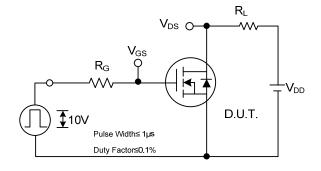


Peak Diode Recovery dv/dt Waveforms

 $V_{\text{DS}} \\$ 

90%

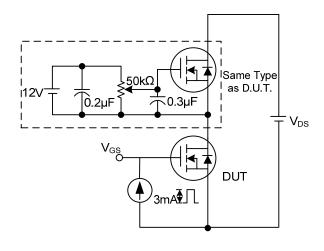
■ TEST CIRCUITS AND WAVEFORMS (Cont.)

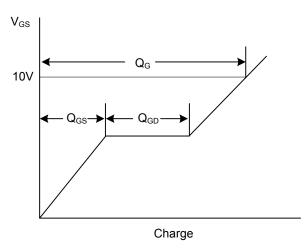


V<sub>GS</sub> 10% → t<sub>D(ON)</sub> → t<sub>D(OFF)</sub> ← t<sub>F</sub> →

**Switching Test Circuit** 

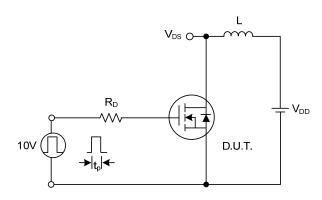
Switching Waveforms

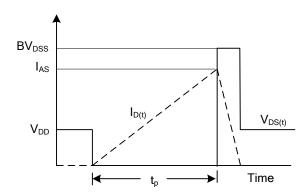




Gate Charge Test Circuit

Gate Charge Waveform





Unclamped Inductive Switching Test Circuit

**Unclamped Inductive Switching Waveforms** 

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